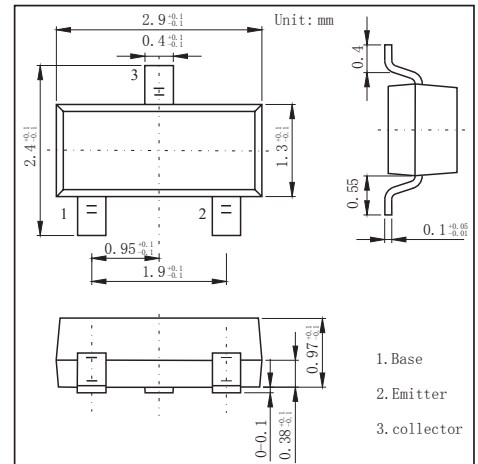


SOT-23 Plastic-Encapsulate Transistors
FEATURES

- General small signal amplifier
- High $h_{FE}=100\sim 320$
- TRANSISTOR NPN

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	35	
Collector-Emitter Voltage	V_{CEO}	30	
Emitter-Base Voltage	V_{EBO}	5	
Collector Current -Continuous	I_C	800	mA
Collector Dissipation	P_C	200	mW
Junction and Storage Temperature	T_j, T_{stg}	-55 to +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_E=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.5	v
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$		120		MHz
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		13		pF